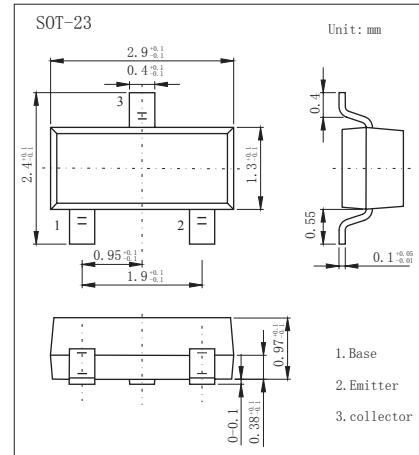


PNP Transistors 2SA1235



■ Features

- Small collector to emitter saturation voltage.
- Excelent lineary DC forward current gain.
- Super mini package for easy mounting.

■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-50	V
Collector-emitter voltage	V _{CE0}	-50	V
Emitter-base voltage	V _{EB0}	-6	V
Collector current	I _c	-200	mA
Collector dissipation (Ta=25°C)	P _c	200	mW
Jumction temperature	T _j	125	°C
Storage temperature	T _{stg}	-55 to +125	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _c = -100 μA, I _E =0	-50			V
Collector- emitter breakdown voltage	V _{CE0}	I _c = -1 mA, I _B =0	-50			
Emitter - base breakdown voltage	V _{EB0}	I _E = -100 μA, I _C =0	-6			
Collector-base cut-off current	I _{CB0}	V _{CB} = -50 V, I _E =0			-0.1	uA
Emitter cut-off current	I _{EB0}	V _{EB} = -6V, I _C =0			-0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-100 mA, I _B =-10mA			-0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-100 mA, I _B =-10mA			-1.2	
DC forward current gain	h _{FE}	V _{CE} = -6V, I _C = -1mA	150		800	
		V _{CE} = -6V, I _C = -0.1mA	90			
Noise figure	NF	V _{CB} = -6V, I _E = 0.3mA, f=100 Hz, R _G =10kΩ			20	dB
Collector output capacitance	C _{ob}	V _{CB} = -6V, I _E = 0, f=1MHz		4		pF
Transition frequency	f _T	V _{CE} = -6V, I _E = -10mA		200		MHz

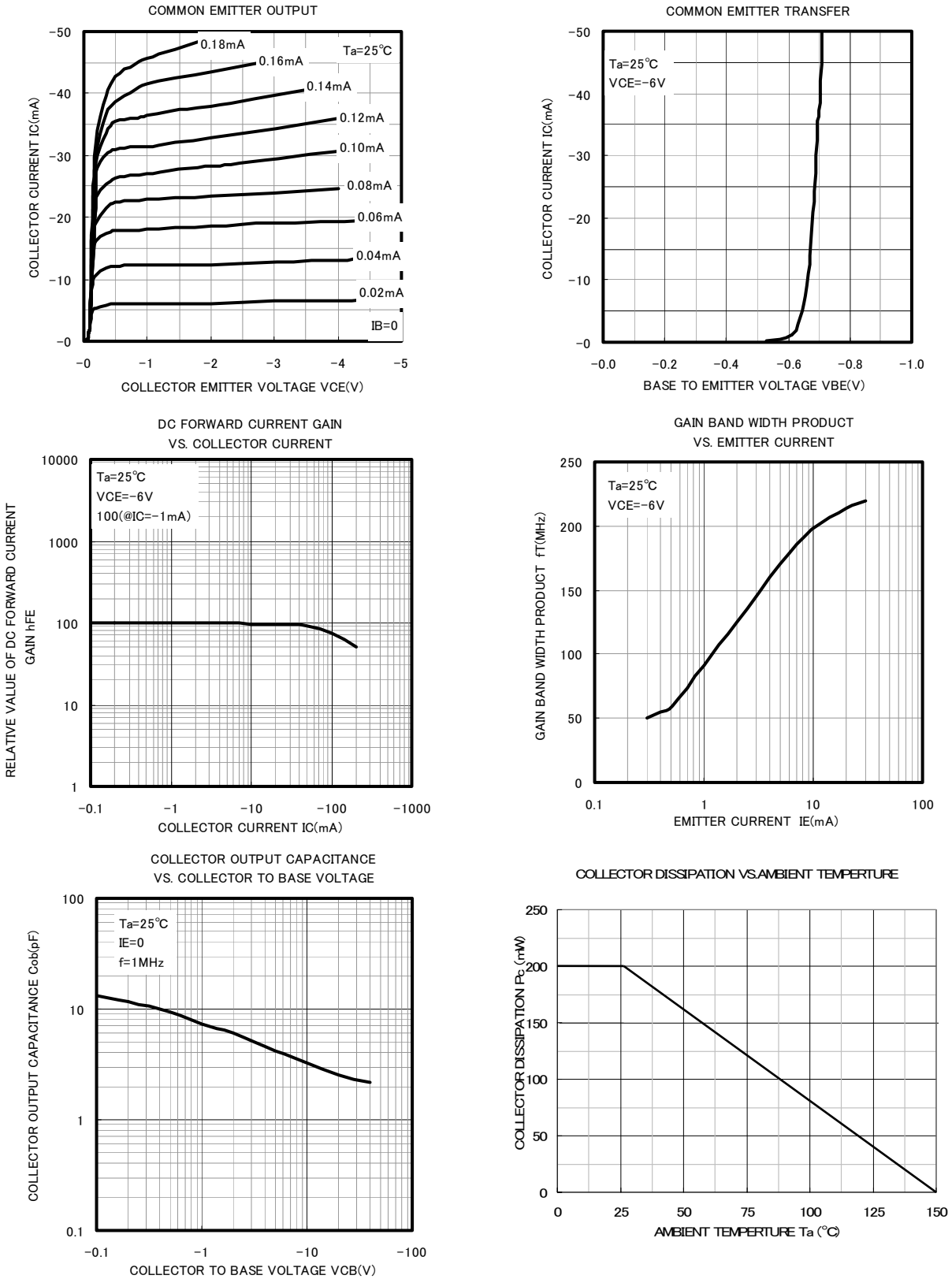
■ Classification of h_{FE}(1)

Type	2SA1235-E	2SA1235-F	2SA1235-G
Range	150-300	250-500	400-800
Marking	ME	MF	MG

PNP Transistors

2SA1235

Typical Characteristics



PNP Transistors

2SA1235

■ Typical Characteristics

